

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-10. (canceled)

11. (currently amended) A method comprising:

forming a first metal layer on a first dielectric layer;

forming a second dielectric layer on the first metal layer;

forming a second metal layer on the second dielectric layer;

patterning the second metal layer such that signal traces are formed in the second metal layer;

patterning the first metal layer as a substantially continuous sheet having slots formed therein in a substantially rectangular pattern to allow the first and second dielectric layers to adhere to each other by way of the slots; and

adjusting an orientation of at least some of the slots in the substantially rectangular pattern such that none of the signal traces passes over any of the slots;

wherein the slots are arrayed substantially in a face-centered rectangular pattern.

12. (original) The method of claim 11, wherein each of the slots has a length:width ratio of at least 5:1.

13. (original) The method of claim 12, wherein the length:width ratio of each slot is at least 10:1.

14. (canceled)

15. (currently amended) The method of claim 14 11, wherein rectangular cells of the pattern have an aspect ratio of substantially 1.73:1.

16. (original) The method of claim 11, wherein a first one of the slots has an orientation that is at an angle relative to an orientation of a second one of the slots.

17. (original) The method of claim 11, wherein each of the slots has a width dimension of substantially 50 microns.

18-27. (canceled)

28. (new) A method comprising:

forming a first metal layer on a first dielectric layer;

forming a second dielectric layer on the first metal layer;

forming a second metal layer on the second dielectric layer;

patterning the second metal layer such that signal traces are formed in the second metal layer;

patterning the first metal layer as a substantially continuous sheet having slots formed therein in a substantially rectangular pattern to allow the first and second dielectric layers to adhere to each other by way of the slots; and

adjusting an orientation of at least some of the slots in the substantially rectangular pattern such that none of the signal traces passes over any of the slots;

wherein each of the slots has a width dimension of substantially 50 microns.

29. (new) A method comprising:

forming a first metal layer on a first dielectric layer;

forming a second dielectric layer on the first metal layer;

forming a second metal layer on the second dielectric layer;

patterning the second metal layer such that signal traces are formed in the second metal layer;

patterning the first metal layer as a substantially continuous sheet having slots formed therein in a substantially rectangular pattern to allow the first and second dielectric layers to adhere to each other by way of the slots; and

adjusting an orientation of at least some of the slots in the substantially rectangular pattern such that none of the signal traces passes over any of the slots;

wherein a first one of the slots has an orientation that is at an angle, other than a right angle, relative to an orientation of a second one of the slots.